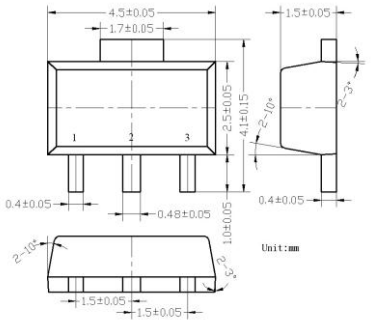
2SB1132 TRANSISTOR (PNP)

Features:

Compliments 2SD1664

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbl	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-32	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1	A
I_{CP}	Collector Current -Pulsed	-2	A
P_C	Collector Power Dissipation	500	mW
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃



1. BASE
2. COLLECTOR
3. EMITTER

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	M ax	Unit
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= -50uA, I_E=0	-40			V
Collector-emitter breakdown voltage *	$V(BR)_{CEO}$	I_C= -1mA, I_B=0	-32			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -50uA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V, I_E=0			-0.5	uA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V, I_C=0			-0.5	uA
DC current gain	$h_{FE(1)}$	V_{CE}= -3V, I_C=-100mA	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA		-0.2	-0.5	V
Transition frequency	f_T	V_{CE}=-5V ,I_C=-50mA,f=30MHZ		150		MHZ
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0,f=1MHZ		20	30	PF

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BAP	BAQ	BAR

Typical Characteristics 2SB1132